

Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney Docket No. 14603-0007US1	Application No. 10/500,079
<b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)		Applicant Jochen Kraft et al.	
		Filing Date March 1, 2005	Group Art Unit 2814

(37 CFR §1.98(b))

**U.S. Patent Documents**

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	1						
	2						
	3						
	4						
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**Foreign Patent Documents or Published Foreign Patent Applications**

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	6							
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	8							
	9							
	10							

**Other Documents (include Author, Title, Date, and Place of Publication)**

Examiner Initial	Desig. ID	Document
/A.M./	11	Greve, D., "Growth of Epitaxial Germanium- Silicon Heterostructures by Chemical Vapour Deposition", Material Science and Engineering, B18, pp. 22-51 (1993).
	12	Lanzerotti, L. D. et al.: "Suppression of Boron Outdiffusion in SiGe HBTs by Carbon Incorporation", IEEE 1996, 0-7803-3393-4.
	13	Osten, H. J. et al.: "Substitutional Versus Interstitial Carbon Incorporation During Pseudomorphic Growth of Si1-yCy on Si(OO1)", Journal of Applied Physics, vol. 80(12), pp. 6711-6715 (1996).
	14	Zerlauth, S. et al.: "Growth Conditions for Complete Substitutional Carbon Incorporation into Si1-yCy Layers Grown by Molecular Beam Epitaxy", Applied Physics Letters, vol. 71(26), pp. 3826-3828 (1997).

Examiner Signature /Anh Mai/	Date Considered 07/20/2009
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EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.